Product data sheet

1. General description

High voltage, high speed, planar passivated NPN power switching transistor in a SOT54 (TO-92) plastic package.

2. Features and benefits

- Fast switching
- · High voltage capability
- · Very low switching and conduction losses

3. Applications

- · Compact fluorescent lamps (CFL)
- Electronic lighting ballasts
- Inverters
- · Off-line self-oscillating power supplies

4. Pinning information

Table 1. Pinning information

Pin	Symbol	Description	Simplified outline	Graphic symbol
1	В	base		С
2	С	collector		В
3	E	emitter	TO-92 (SOT54)	E sym123

5. Ordering information

Table 2. Ordering information

Type number	Package				
	Name	Description	Version		
PHE13003A	TO-92	plastic single-ended leaded (through hole) package; 3 leads	SOT54		

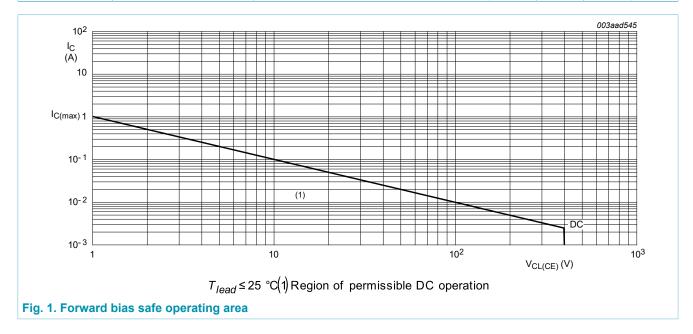
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6. Limiting values

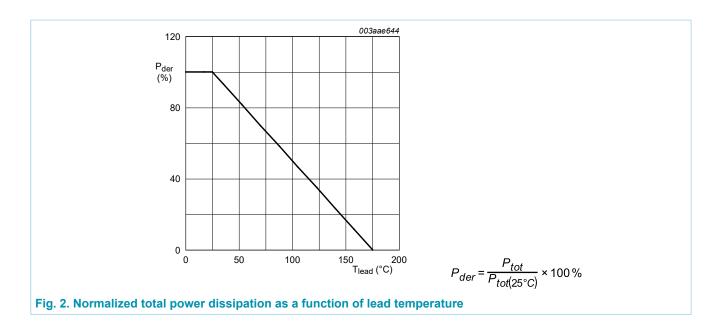
Table 3. Limiting values

In accordance with the Absolute Maximum Rating System (IEC 60134).

Symbol	Parameter	Conditions	M	in Max	Unit
V _{CESM}	collector-emitter peak voltage	V _{BE} = 0 V	-	700	V
V_{CBO}	collector-base voltage	I _E = 0 A	-	700	V
V_{CEO}	collector-emitter voltage	I _B = 0 A	-	400	V
V_{EBO}	emitter-base voltage	I _C = 0 A; I(Emitter) = 10 mA	-	9	V
I _C	collector current	DC; Fig. 1	-	1	Α
I _{CM}	peak collector current		-	2	Α
I _B	base current	DC	-	0.5	Α
I _{BM}	peak base current		-	1	Α
P _{tot}	total power dissipation	T _{lead} ≤ 25 °C; <u>Fig. 2</u>	-	2.1	W
T _{stg}	storage temperature		-6	5 150	°C
Tj	junction temperature		-	150	°C



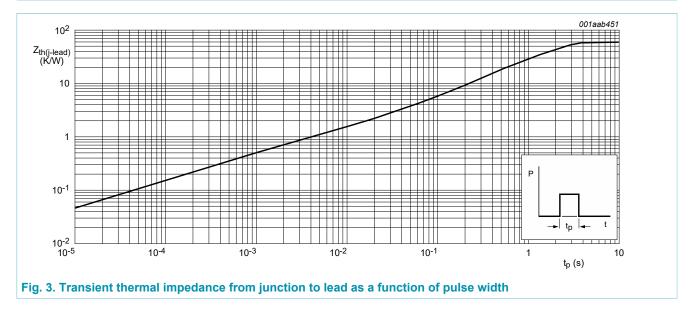
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7. Thermal characteristics

Table 4. Thermal characteristics

Symbol	Parameter	Conditions	Min	Тур	Max	Unit
R _{th(j-lead)}	thermal resistance from junction to lead	<u>Fig. 3</u>	-	-	60	K/W
R _{th(j-a)}	thermal resistance from junction to ambient free air	printed circuit board mounted; lead length = 4 mm	-	150	-	K/W



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8. Characteristics

Table 5. Characteristics

Symbol	Parameter	Conditions	M	in Typ	Max	Unit
Static chara	acteristics					
I _{CES}	collector-emitter cut-off current (base shorted)	$V_{BE} = 0 \text{ V}; V_{CE} = 700 \text{ V}; T_j = 125 \text{ °C}$	-	-	5	mA
I _{EBO}	emitter-base cut-off current (collector open)	$V_{EB} = 9 \text{ V}; I_{C} = 0 \text{ A}; T_{lead} = 25 ^{\circ}\text{C}$	-	-	1	mA
V_{CEOsus}	collector-emitter sustaining voltage (base open)	$I_B = 0 \text{ A}; I_C = 1 \text{ mA}; L_C = 25 \text{ mH};$ $T_{lead} = 25 \text{ °C}; \underline{Fig. 4}; \underline{Fig. 5}$	40	00 -	-	V
V _{CEsat}	collector-emitter saturation voltage	I_C = 0.25 A; I_B = 50 mA; T_{lead} = 25 °C; Fig. 6	-	0.2	0.5	V
		I_C = 0.5 A; I_B = 125 mA; T_{lead} = 25 °C; Fig. 6	-	0.3	1	V
		I_C = 0.75 A; I_B = 250 mA; T_{lead} = 25 °C; Fig. 6	-	0.4	1.5	V
V _{BEsat}	base-emitter saturation voltage	$I_C = 0.25 \text{ A}$; $I_B = 50 \text{ mA}$; $T_{lead} = 25 ^{\circ}\text{C}$; Fig. 7	-	-	1	V
		I_C = 0.5 A; I_B = 125 mA; T_{lead} = 25 °C; Fig. 7	-	-	1.2	V
h _{FE}	DC current gain	I_C = 0.5 mA; V_{CE} = 2 V; T_{lead} = 25 °C; Fig. 8; Fig. 9	12	2 -	-	
		$I_C = 0.4 \text{ A}; V_{CE} = 5 \text{ V}; T_{lead} = 25 ^{\circ}\text{C};$ Fig. 8; Fig. 9	10) -	30	
		I _C = 0.8 A; V _{CE} = 5 V; T _{lead} = 25 °C; <u>Fig. 8</u> ; <u>Fig. 9</u>	5	7.5	20	
Dynamic ch	aracteristics					
t _f	fall time	I_C = 1 A; I_{Bon} = 200 mA; V_{BB} = -5 V; L_B = 1 μ H; T_{lead} = 25 °C; inductive load; Fig. 10; Fig. 11	-	80	-	ns

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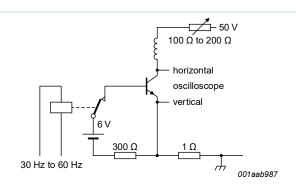


Fig. 4. Test circuit for collector-emitter sustaining voltage

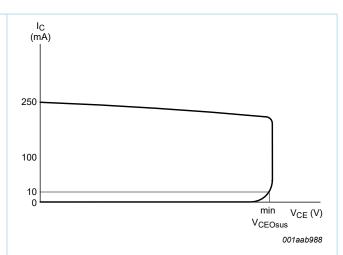


Fig. 5. Oscilloscope display for collector-emitter sustaining voltage test waveform

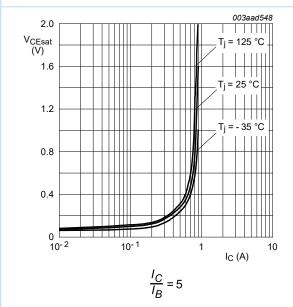


Fig. 6. Collector-emitter saturation voltage as a function of collector current; typical values

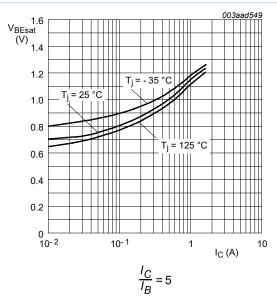


Fig. 7. Base-emitter saturation voltage as a function of collector current; typical values

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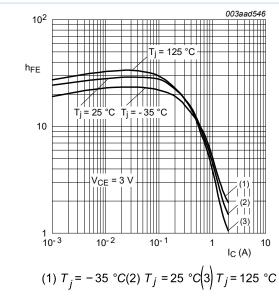


Fig. 8. DC current gain as a function of collector current; typical values

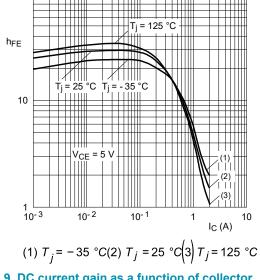
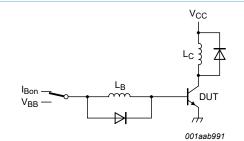


Fig. 9. DC current gain as a function of collector current; typical values



 $V_{CC} = 300 \ V; V_{BB} = -5 \ V; L_C = 200 \ \mu H; L_B = 1 \ \mu H$

Fig. 10. Test circuit for inductive load switching

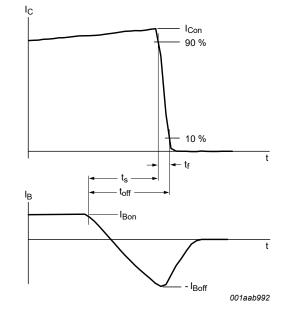


Fig. 11. Switching times waveforms for inductive load

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9. Package outline

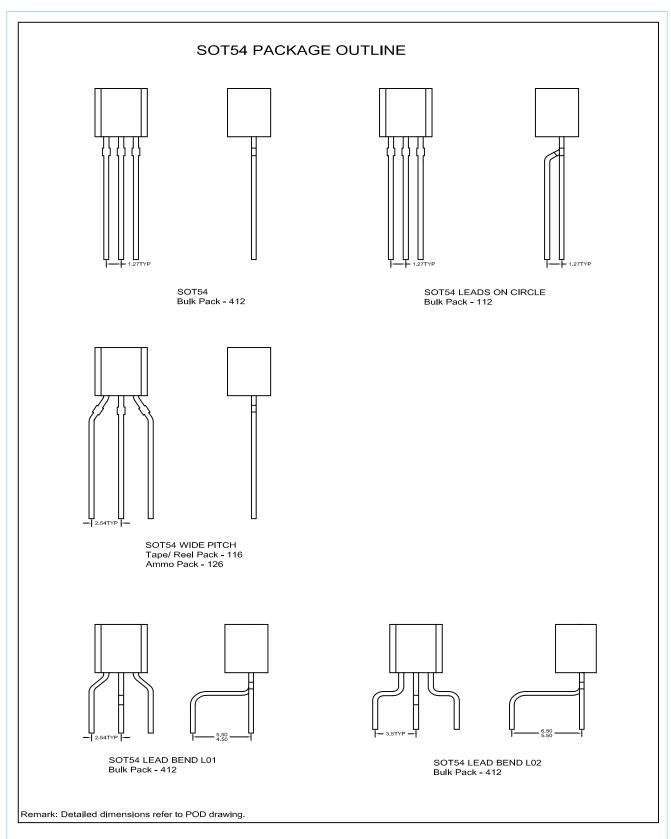


Fig. 12. Package outline TO-92 (SOT54)

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10. Legal information

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Document status [1][2]	Product status [3]	Definition
Objective [short] data sheet	Development	This document contains data from the objective specification for product development.
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Product [short] data sheet	Production	This document contains the product specification.

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- [2] The term 'short data sheet' is explained in section "Definitions".
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